Program

Saturday, September 13
Arrival

Sunday, September 14
10:00  Technical session on “History of electronics”, Technische Universität, Campus in the Deutsches Museum
12:30 Lunch
14:00 Tour of the Main Campus of Technische Universität München

Monday, September 15, Seminarraum, Walter Schottky Institut
9:00  Registration
9:15 Opening address: Prof. Gerhard Abstreiter, Geschäftsführender Direktor des Walter Schottky Instituts, TUM
Scientific Sessions
9:30  “Near field spectroscopy of quantum dots”, Toshiharu Saiki, Keio University
10:00 “Electrically tunable single dot nanocavities”, Jon Finley, Technische Universität München
10:30 Coffee Break
10:45 “Spin Hall effects coupled with magnetization dynamics in a metallic film”, Eiji Saitoh, Keio University
11:15 “Spin wave dynamics in antidot lattices”, Bernhard Botters, Technische Universität München
12:00 Lunch
13:15 “Electronic states, transport and Kondo effect in semiconductor quantum dots”, Mikio Eto, Keio University
13:45 “Nextnano: a simulation package for 3D nanometer semiconductor structures”, Peter Vogl, Technische Universität München
14:15 Coffee Break
14:30 Poster session, Foyer, Walter Schottky Institut
15:45 “Photo-switchable magnetic materials at room temperature”, Yasuaki Einaga, Keio University
16:15 “Triplet supercurrent through a half-metallic ferromagnet”, Sebastian Goennenwein, Walther-Meissner-Institut, Bayerische Akademie der Wissenschaften
18:30 Dinner at “Hofbräukeller“, Wiener Platz
Tuesday, September 16, Seminarraum, Walter Schottky Institut

Scientific Sessions

9:30  “Carbon nanotube electronic and optoelectronic devices”,
      Hideyuki Maki, Keio University
10:00 “Mesoscopic optoelectronic transport across lithographically defined quantum wires.”
      Klaus-Dieter Hof, Ludwig-Maximilians-Universität
10:30 Coffee Break
10:45 “Quantum filtering and feedback control”,
      Naoki Yamamoto, Keio University
11:15 “Optimal control of spin and pseudo-spin systems”,
      Steffen Glaser, Technische Universität München
12:00 Lunch
13:15 “Helium-4 in nanoporous media: Quantum phase transition, localized Bose-Einstein condensation, and supersolid”,
      Keiya Shirahama, Keio University
13:45 “Viscous transport in Fermi superfluids”,
      Dietrich Einzel, Walther-Meissner-Institut, Bayerische Akademie der Wissenschaften
14:15 Coffee Break
14:30 “Silicon quantum computers”,
      Kohei Itoh, Keio University
15:00 “Read-out of phosphorus donor spin states”,
      Martin Brandt, Technische Universität München
16:00 Lab tours

Wednesday, September 17

Scientific Session

9:30  Student mixer, Seminarraum, Walter Schottky Institut
12:00 Lunch
13:15 Tour of the Walter Schottky Institut
16:30 Closing: Prof. Martin Brandt, Seminarraum, Walter Schottky Institut

Thursday, September 18

Departure
List of poster presenters:

Technische Universität München
Andre R. Stegner, “Phosphorus donors in freestanding silicon quantum dots”
Franz D. Czeschka, “Magnetic anisotropy of (100)- and (110)-oriented CrO₂ thin films”
Simone Kaniber, "Optoelectronic properties of hybrids made of the photosynthetic reaction center (PS I) and carbon nanotubes"
Christoph Bihler, “Hydrogen in GaN:Mn”
Robert Fischer, “Tools for the coherent control of finite dimensional quantum systems”
Sebastian Neusser, “Spin dynamics in ferromagnetic antidot lattices”

Keio University
Fukutaro Hamaoka, “Numerical prediction of a cicro-scale etching of Si under plasma molding in 2f-CCP in SF₆/O₂”
Yasuo Shimizu, “Nano-CMOS process monitoring by silicon isotopes”
Satoru Miyamoto, “Escape dynamics of few electrons in a single-electron ratchet using silicon nanowire MOSFETs”
Hiroki Morishita, “Electrical readout of Bell states of phosphorus in silicon”
Toyofumi Ishikawa, “Zeeman study about the isoelectronic beryllium pair center in silicon”
Tatsumasa Itahashi, “Dynamic nuclear polarization of \(^{29}\)Si via the neutral (S=1) one-vacancy-oxygen center in isotopically controlled silicon”
Shinichi Tojo, “Pulsed electron spin resonance in phosphorus doped isotopically controlled silicon”
Go Tsuchiya, “Estimation of transport properties of two-dimensional electron gas in strained Si/SiGe heterostructures”
Mohammad Rizwanur Rahman, “\(T_1\) measurement of \(^{29}\)Si nuclei in phosphorus-doped isotopically controlled silicon by inversion recovery method”
Hiroyuki Tezuka, “The isotope effect in EPR line shape of boron in silicon”
Katsuhiro Naito, “Optical and electrical characterization of beryllium doped silicon”
Rii Hirano, “Photoluminescence of Si/SiGe nanocolumn”
Kei Yoshizawa, “Host isotope effects on Be₂ bound exciton luminescence in Si”